

Title (en)

Process and system for fabrication of patterns on a surface

Title (de)

Verfahren und System zur Herstellung von Strukturen auf einer Oberfläche

Title (fr)

Procédé et système de fabrication de motifs sur une surface

Publication

EP 2144117 A1 20100113 (EN)

Application

EP 08104722 A 20080711

Priority

EP 08104722 A 20080711

Abstract (en)

The invention provides a system and process of patterning structures on a surface comprising exposing part of the surface to an ion flux, such that material properties of the exposed surface are modified to provide a mask effect on the surface. A further step of etching unexposed parts of the surface forms the structures on the surface. The inventors have discovered that by controlling the ion exposure, alteration of the surface structure at the top surface provides a mask pattern, without substantially removing any material from the exposed surface. The mask allows for subsequent ion etching of unexposed areas of the surface leaving the exposed areas raised relative to the unexposed areas thus manufacturing patterns onto the surface. For example, a Ga⁺ focussed ion beam exposes a pattern onto a diamond surface which produces such a pattern after its exposure to an oxygen plasma etch. The invention is particularly suitable for patterning of clear well-defined structures down to nano-scale dimensions.

IPC 8 full level

G03F 7/11 (2006.01); **B81C 1/00** (2006.01); **G03F 7/00** (2006.01); **H01L 21/033** (2006.01)

CPC (source: EP US)

B81C 1/00634 (2013.01 - EP US); **B82Y 10/00** (2013.01 - EP US); **B82Y 40/00** (2013.01 - EP US); **G03F 7/0002** (2013.01 - EP US); **G03F 7/11** (2013.01 - EP US); **H01L 21/0337** (2013.01 - EP US); **B81C 2201/0143** (2013.01 - EP US); **B81C 2201/0159** (2013.01 - EP US); **B81C 2201/036** (2013.01 - EP US); **Y10T 428/24802** (2015.01 - US)

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Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MT NL NO PL PT RO SE SI SK TR

Designated extension state (EPC)

AL BA MK RS

DOCDB simple family (publication)

EP 2144117 A1 20100113; AU 2009267415 A1 20100114; EP 2310911 A1 20110420; EP 2310911 B1 20170517; EP 3276418 A1 20180131; EP 3276418 B1 20200909; US 2011189446 A1 20110804; US 8524100 B2 20130903; WO 2010003600 A1 20100114

DOCDB simple family (application)

EP 08104722 A 20080711; AU 2009267415 A 20090703; EP 09793879 A 20090703; EP 17171301 A 20090703; EP 2009004846 W 20090703;
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